# Silicon Carbide Schottky Diode

650 V, 6 A

## FFSD0665B

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 24.5 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Applications**

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

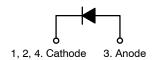
Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage		$V_{RRM}$	650	V
Single Pulse Avalanche Energy ( $T_J = 25^{\circ}C$ , $I_{L(pk)} = 9.9$ A, $L = 0.5$ mH, $V = 50$ V)		E <sub>AS</sub>	24.5	mJ
Continuous Rectified Forward Current	T <sub>C</sub> < 154	IF	6.0	Α
Current	T <sub>C</sub> < 135		9.1	
Non-Repetitive Peak Forward Surge Current	$T_C = 25^{\circ}C$ , $t_P = 10 \mu s$	I <sub>FM</sub>	493	Α
	$T_{C} = 150^{\circ}C,$ $t_{P} = 10 \ \mu s$		442	
Non-Repetitive Forward Surge Current (Half-Sine Pulse)	$T_C = 25$ °C $t_P = 8.3$ ms	I <sub>FSM</sub>	28	Α
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>tot</sub>	75	W
	T <sub>C</sub> = 150°C		12.5	
Operating Junction and Storage T Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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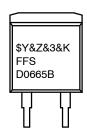


**Schottky Diode** 



DPAK3 (TO-252, 3 LD) CASE 369AS

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code

&3 = Numeric Date Code

K = Lot Code

FFSD0665B = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

#### FFSD0665B

#### THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	2.0	°C/W

#### **ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
ON CHARAC	TERISTICS			•		•
$V_{F}$	Forward Voltage	I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 25°C		1.38	1.7	V
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125°C		1.53	2.0	
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 175°C		1.67	2.4	
I <sub>R</sub> Reverse Curre	Reverse Current	V <sub>R</sub> = 650 V, T <sub>J</sub> = 25°C		0.5	40	μΑ
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 125°C		1.0	80	1
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 175°C		2.0	160	1
CHARGES, C	APACITANCES & GATE RES	ISTANCE				
Q <sub>C</sub>	Total Capacitive Charge	V <sub>C</sub> = 400 V		16		nC
C <sub>tot</sub>		V <sub>R</sub> = 1 V, f = 100 kHz		259		pF
		V <sub>R</sub> = 200 V, f = 100 kHz		29		1
		V <sub>R</sub> = 400 V, f = 100 kHz		22		1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method <sup>†</sup>	Reel Size	Tape Width	Quantity
FFSD0665B	FFSD0665B	DPAK3	Tape & Reel	330 mm	16 mm	2500 units

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### FFSD0665B

#### **TYPICAL CHARACTERISTICS**

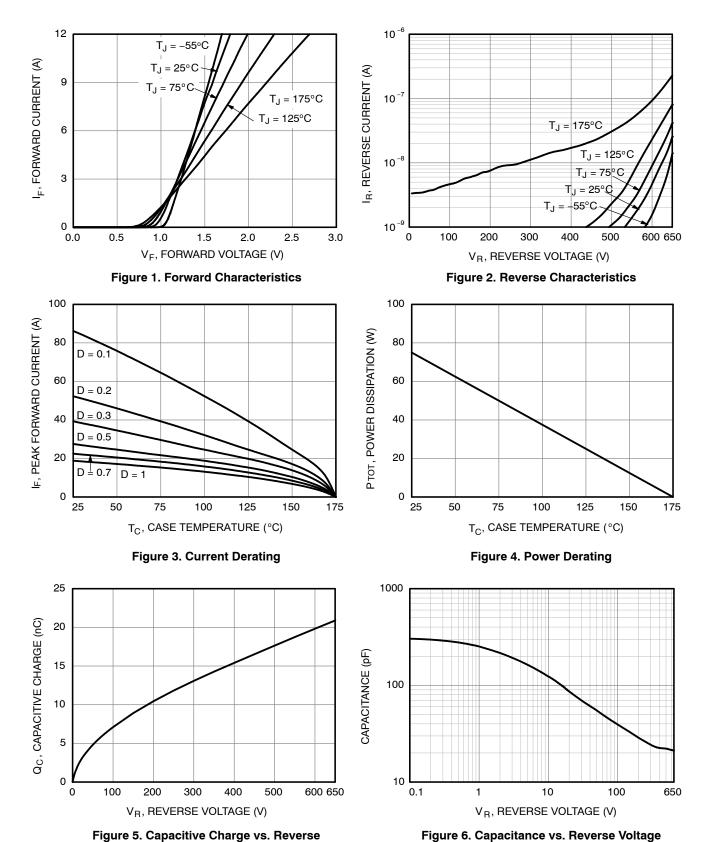


Figure 6. Capacitance vs. Reverse Voltage

Voltage

## FFSD0665B

## TYPICAL CHARACTERISTICS(continued)

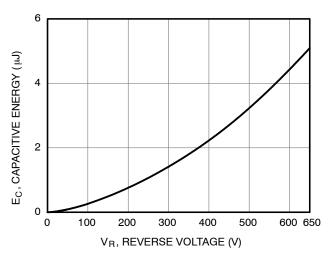


Figure 7. Capacitance Stored Energy

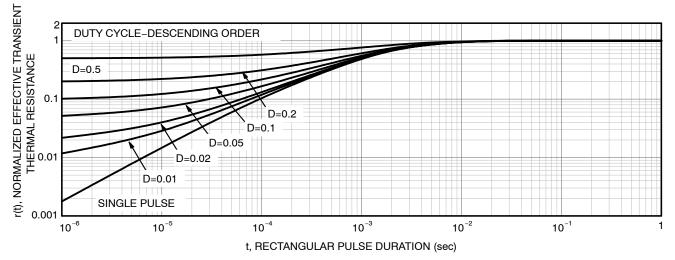
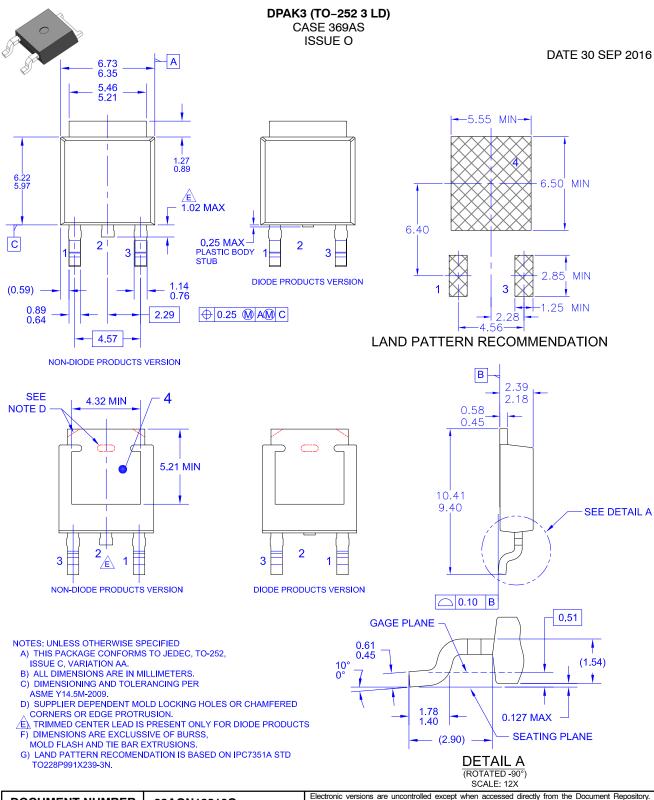


Figure 8. Junction-to-Case Transient Thermal Response





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DESCRIPTION:	DPAK3 (TO-252 3 LD)		PAGE 1 OF 1	

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